

November 2013

FDP65N06

N-Channel UniFETTM MOSFET 60 V, 65 A, 16 m Ω

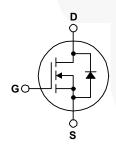
Features

- $R_{DS(on)}$ = 13 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 32.5 A
- Low Gate Charge (typical 33 nC)
- Low Crss (typical 35 pF)
- · Fast Switching
- · Improved dv/dt Capability

Description

UniFET™ MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





Absolute Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol	Parameter		FDP65N06	Units
V _{DSS}	Drain-Source Voltage		60	V
I _D	Drain Current - Continuous (T _C = 25°C)		65	Α
	- Continuous (T _C = 100°C)		41	Α
I _{DM}	Drain Current - Pulsed	(Note 1)	260	Α
V _{GSS}	Gate-Source Voltage		± 20	V
E _{AS}	Single Pulsed Avalanche Energy	(Note 2)	430	mJ
I _{AR}	Avalanche Current	(Note 1)	65	А
E _{AR}	Repetitive Avalanche Energy	(Note 1)	13.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P _D	Power Dissipation (T _C = 25°C) - Derate above 25°C		135	W
			1.08	W/°C
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T _L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	°C	

Thermal Characteristics

Symbol	Parameter	FDP65N06	Units	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.92	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP65N06	FDP65N06	TO-220	Tube N/A		50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Units
Off Charac	teristics					
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	60	-	-	V
ΔBV_{DSS} / ΔT_{J}	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	-	0.5	-	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 60 V, V _{GS} = 0 V	-	-	1	μΑ
		$V_{DS} = 48 \text{ V}, T_{C} = 125^{\circ}\text{C}$	-	-	10	μΑ
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 20 V, V _{DS} = 0 V	-	-	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -20 V, V _{DS} = 0 V	-	-	-100	nA
On Charact	eristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	2.0	-	4.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 32.5 A	-	0.013	0.016	Ω
g _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 32.5 A	-	39	-	S
Dynamic Ch	haracteristics					
C _{iss}	Input Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$	\-	1670	2170	pF
C _{oss}	Output Capacitance	f = 1.0 MHz	-	464	600	pF
C _{rss}	Reverse Transfer Capacitance		-\	35	52	pF
Switching C	Characteristics			I		
t _{d(on)}	Turn-On Delay Time	$V_{DD} = 30 \text{ V}, I_{D} = 65\text{A},$	-	24	58	ns
t _r	Turn-On Rise Time	$R_G = 25 \Omega$	-	94	200	ns
t _{d(off)}	Turn-Off Delay Time		-	98	210	ns
t _f	Turn-Off Fall Time	(Note 4)	-	52	114	ns
Qg	Total Gate Charge	V _{DS} = 48 V, I _D = 65A,	-	33	43	nC
Q _{gs}	Gate-Source Charge	V _{GS} = 10 V	/-	10	-	nC
Q _{gd}	Gate-Drain Charge	(Note 4)	-	11	-	nC
Drain-Source	ce Diode Characteristics and Maximum Ratings			I	7	
I _S Maximum Continuous Drain-Source Diode Forward Current			-	-	65	Α
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current			-	260	Α
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 65 A	-	-	1.4	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 65 A,	- 17	62	//	ns
Q _{rr}	Reverse Recovery Charge	$dI_{F}/dt = 100 \text{ A/}\mu\text{s}$	-	132		nC

NOTES

^{1.} Repetitive Rating: Pulse width limited by maximum junction temperature.

^{2.} L = 47 μ H, I_{AS} = 65 A, V_{DD} = 50 V, R_G = 25 Ω , Starting T_J = 25°C.

^{3.} $I_{SD} \le 65$ A, di/dt ≤ 200 A/ μ s, $V_{DD} \le BV_{DSS}$, Starting $T_J = 25^{\circ}C$.

^{4.} Essentially independent of operating temperature.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

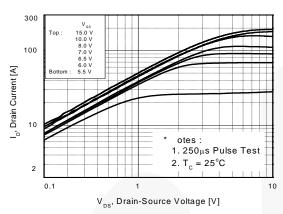


Figure 3. On-Resistance Variation vs.

Drain Current and Gate Voltage

Figure 2. Transfer Characteristics

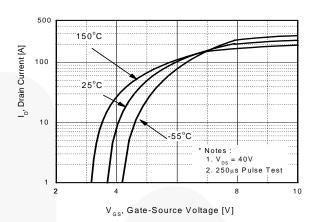
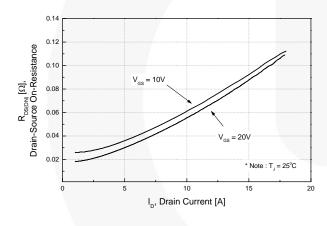


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue



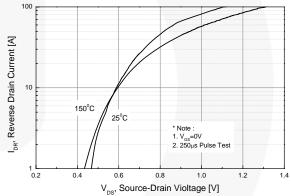


Figure 5. Capacitance Characteristics

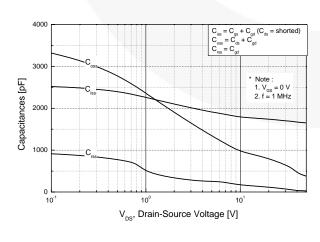
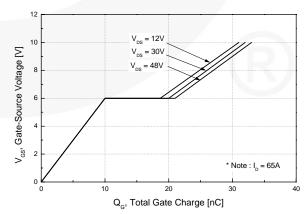


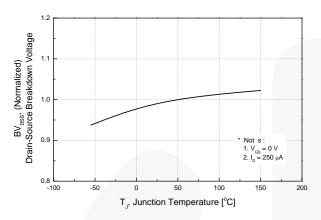
Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



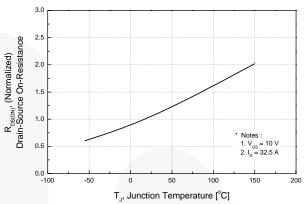
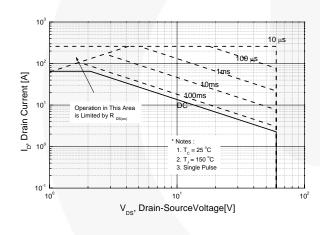


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature



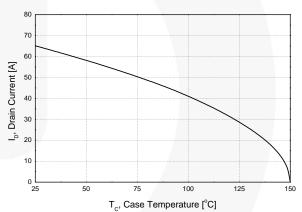


Figure 11. Transient Thermal Response Curve

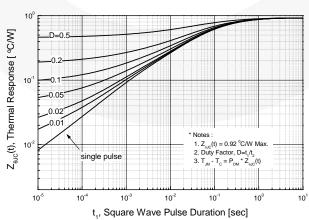


Figure 12. Gate Charge Test Circuit & Waveform

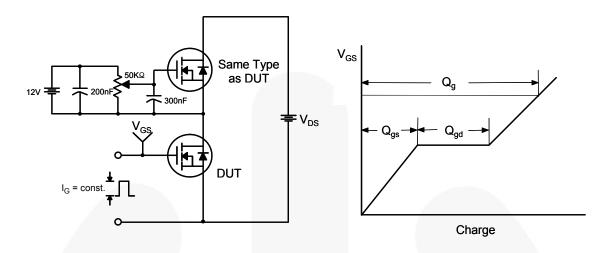


Figure 13. Resistive Switching Test Circuit & Waveforms

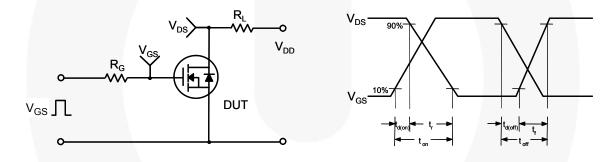
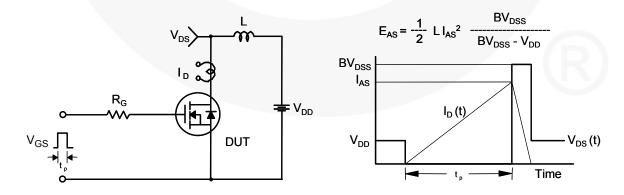


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



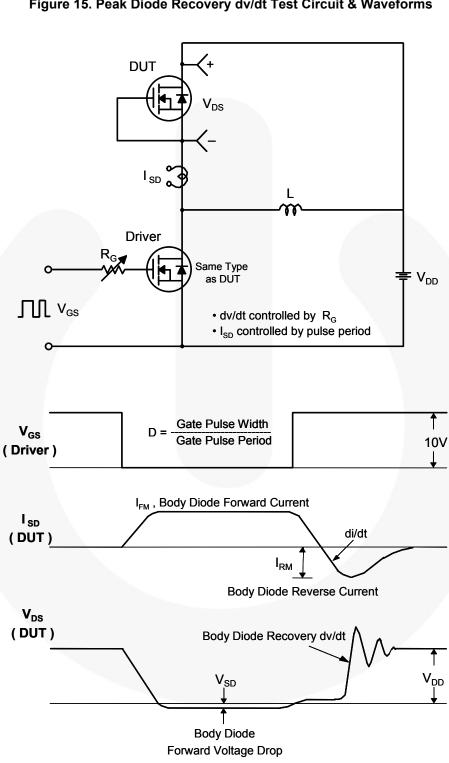


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

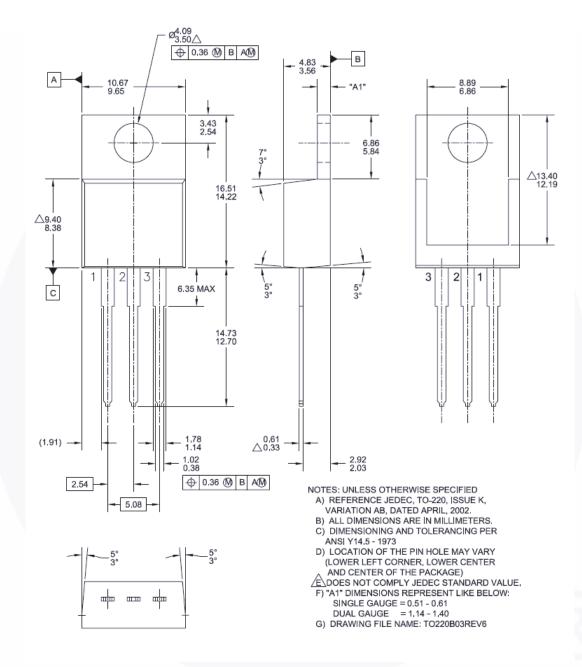


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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